**Measurement of:** Analysis of current versus voltage (IV) characteristics of semiconducting/ conducting samples.

**Equipment:** Source measure unit

**Property Measured:**

This system is useful for the analysis of current versus voltage (IV) characteristics of semiconducting/ conducting samples. The system can be utilised for the analysis of both top & bottom GATE dependant studies (field effect transconductance studies) on transistors having a few micrometer channel length on silicon wafer upto femtoampere (FA) accuracy when connected with a micro probe station.

**Photograph (small size)**

**Basic Principle:**

The system can be utilised for the analysis of both top & bottom GATE dependant studies (field effect transconductance studies) on transistors having a few micrometer channel length on silicon wafer upto femtoampere (FA) accuracy when connected with a micro probe station.

**Capabilities:**

analysis of current versus voltage (IV) characteristics of semiconducting/ conducting samples.

**Sample Requirement:** Less than 1"